

FEATURES

Complimentary to S9014

MARKING: M6
MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-50	V
Collector-Emitter Voltage	V _{CEO}	-45	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current -Continuous	I _C	-0.1	A
Collector Power Dissipation	P _C	0.2	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

S9015 (PNP)

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CBO}	I _C = -100μA, I _E = 0	-50			V
Collector-emitter breakdown voltage	V _{CEO}	I _C = -0.1mA, I _B = 0	-45			V
Emitter-base breakdown voltage	V _{EBO}	I _E = -100μA, I _C = 0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} = -50 V, I _E = 0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -5V, I _C = 0			-0.1	μA
DC current gain	h _{FE}	V _{CE} = -5V, I _C = -1mA	200		1000	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -100mA, I _B = -10mA			-0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = -100mA, I _B = -10mA			-1	V
Transition frequency	f _T	V _{CE} = -5V, I _C = -10mA f = 30MHz	150			MHz

CLASSIFICATION OF h_{FE}

Rank	L	H
Range	200-450	450-1000

S9015 Typical Characteristics

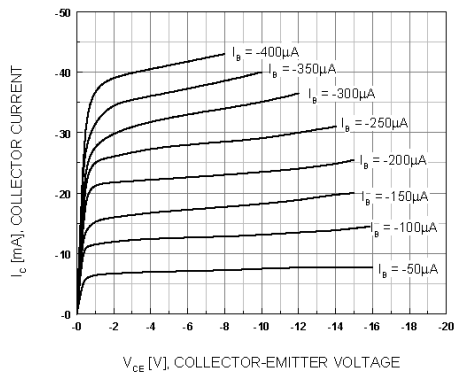


Figure 1. Static Characteristic

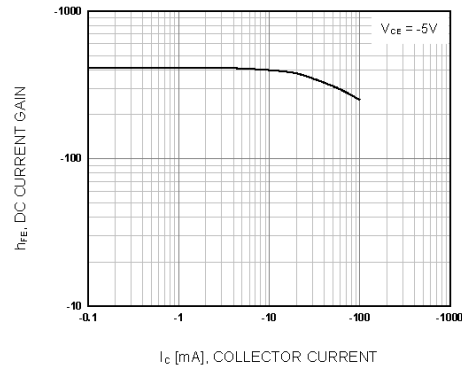


Figure 2. DC current Gain

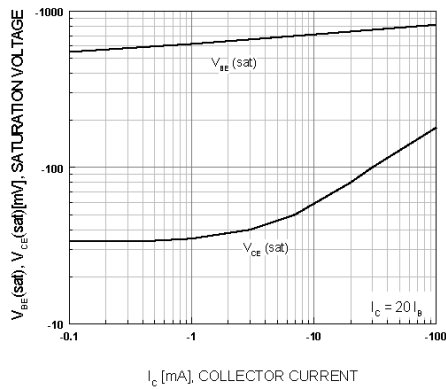


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

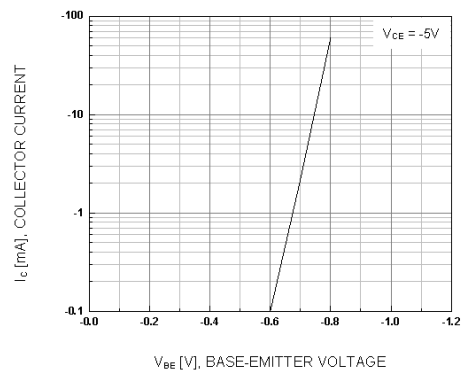


Figure 4. Base-Emitter On Voltage

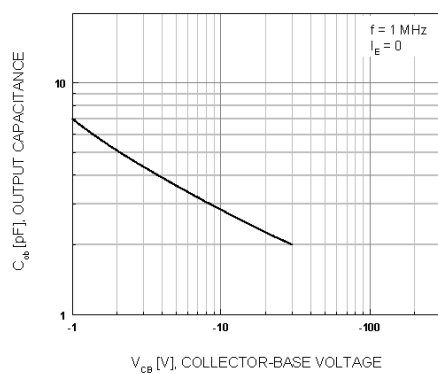


Figure 5. Collector Output Capacitance

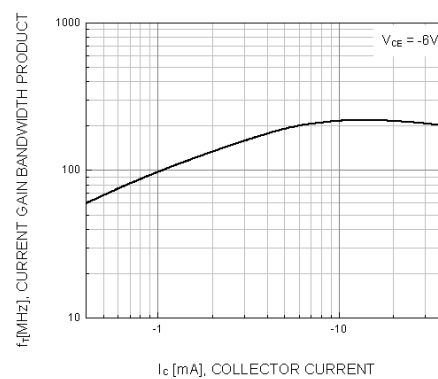


Figure 6. Current Gain Bandwidth Product